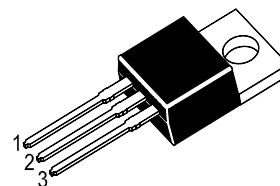


2SK1118

N-Channel Enhancement Mode Field Effect Transistor

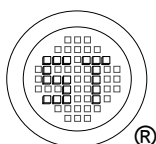


1.Base 2.Collector 3.Emitter

TO-220 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	600	V
Collector Emitter Voltage	V_{CEO}	600	V
Emitter Base Voltage	V_{EBO}	± 30	V
Collector Current	I_{C}	6	A
Collector Current (Pulse)	I_{CP}	24	A
Power Dissipation ($T_c = 25^\circ\text{C}$)	P_{tot}	45	W
Thermal Resistance Junction to Ambient	$R_{\theta\text{JA}}$	62.5	$^\circ\text{C/W}$
Thermal Resistance Junction to Case	$R_{\theta\text{JC}}$	2.77	$^\circ\text{C/W}$
Junction Temperature	T_{j}	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$



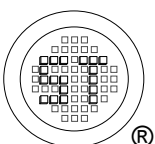
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Dated : 04/01/2016 Rev:01

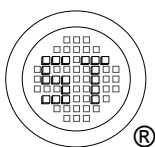
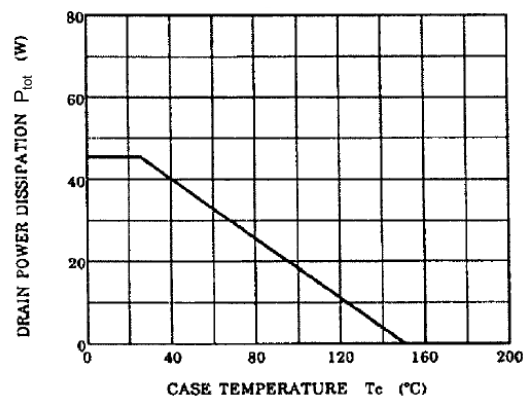
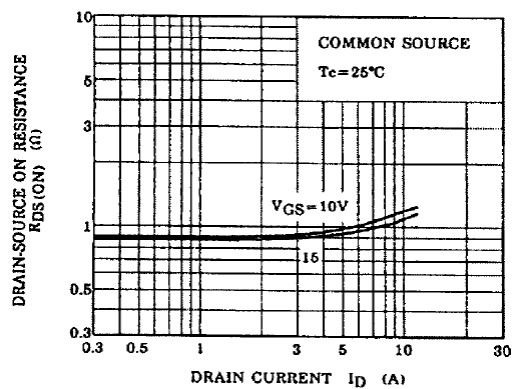
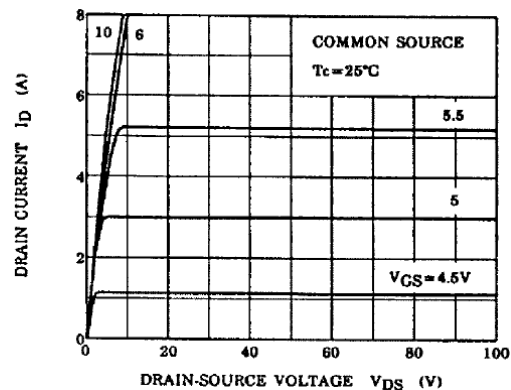
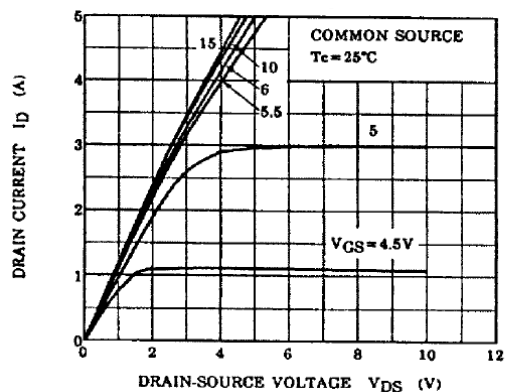
Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage at $I_D = 10\text{ mA}$	$V_{(BR)DSS}$	600	-	-	V
Drain-Source Leakage Current at $V_{DS} = 600\text{ V}$	I_{DSS}	-	-	300	μA
Gate-Source Leakage Current at $V_{GS} = \pm 25\text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at $V_{DS} = 10\text{ V}$, $I_D = 1\text{ mA}$	$V_{GS(th)}$	1.5	-	3.5	V
Drain-Source On-State Resistance at $V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$	$R_{DS(on)}$	-	-	1.25	Ω
Forward Transconductance at $V_{DS} = 10\text{ V}$, $I_D = 3\text{ A}$	g_{FS}	3	-	-	S
Input Capacitance at $V_{DS} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{iss}	-	-	2000	pF
Output Capacitance at $V_{DS} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{oss}	-	-	380	pF
Reverse Transfer Capacitance at $V_{DS} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{rss}	-	-	120	pF
Turn-On Delay Time at $V_{DD} = 300\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$, $R_L = 100\ \Omega$	$t_{d(on)}$	-	-	80	ns
Turn-On Rise Time at $V_{DD} = 300\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$, $R_L = 100\ \Omega$	t_r	-	-	50	ns
Turn-Off Delay Time at $V_{DD} = 300\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$, $R_L = 100\ \Omega$	$t_{d(off)}$	-	-	170	ns
Turn-Off Fall Time at $V_{DD} = 300\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$, $R_L = 100\ \Omega$	t_f	-	-	40	ns



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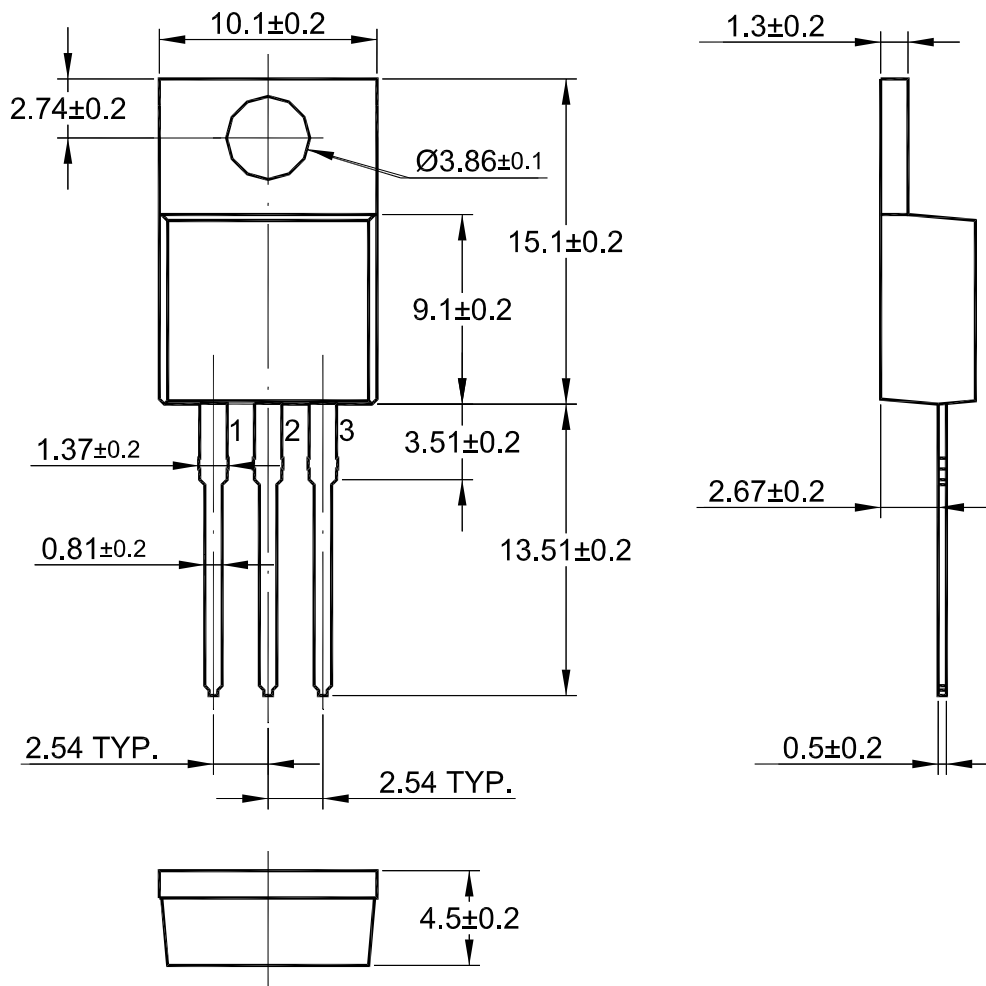




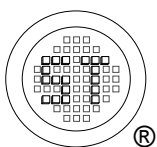
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TO-220 Package Outline



Dimensions in mm



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